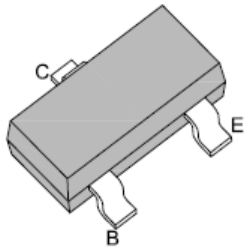
SMD General Purpose Transistor (PNP)



SOT-23

Features

- PNP Silicon Epitaxial Planar Transistor for Switching and Amplifier Applications
- RoHS compliance

Mechanical Data

Case:	SOT-23, Plastic Package
Terminals:	Solderable per MIL-STD-202G, Method 208
Weight:	0.008 gram

Maximum Ratings *(T Ambient=25ºC unless noted otherwise)*

Symbol	Description	MMBT3906	Unit	Conditions
V_{CEO}	Collector-Emitter Voltage	-40	V	
V_{CBO}	Collector-Base Voltage	-40	V	
V_{EBO}	Emitter-Base Voltage	-5.0	V	
I_C	Collector Current	-200	mA	
P_D	Total Device Power Dissipation(Note 1)	225	mW	T_A=25 ˚C
		1.8	mW/°C	Derate above 25 ˚C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	556	°C /W	
P_D	Total Device Power Dissipation, Alumina Substrate (Note 2)	300	mW	T_A=25 ˚C
		2.4	mW/°C	Derate above 25 ˚C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	417	°C /W	
T_J	Junction Temperature	-55 to +150	°C	
T_{STG}	Storage Temperature Range	-55 to +150	°C	

Note: 1. FR-5 Board=25.4 x 19.05 x 1.58 mm (1.0 x 0.75 x 0.062 inches.)
2. Alumina Substrate=10.16 x 7.62 x 0.61 mm (0.4 x 0.3 x 0.024 inches.) 99.5% alumina.

Electrical Characteristics *($T_{Ambient}$=25ºC unless noted otherwise)*

Off Characteristics

Symbol	Description	Min.	Max.	Unit	Conditions
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (Pulse width ≤300μs, Duty Cycle ≤2.0%)	-40	-	V	I_C=-1mA, I_B=0
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	-40	-	V	I_C=-10μA, I_E=0
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	-5.0	-	V	I_E=-10μA, I_C=0
I_{BL}	Base Cut-off Current	-	-50	nA	V_{EB}=-3V, V_{CE}=-30V
I_{CEX}	Collector Cut-off Current	-	-50	nA	V_{EB}=-3V, V_{CE}=-30V

On Characteristics

Symbol	Description	Min.	Max.	Unit	Conditions
h_{FE}	D.C. Current Gain	60	-		V_{CE}=-1V, I_C=-0.1mA
		80	-		V_{CE}=-1V, I_C=-1mA
		100	300		V_{CE}=-1V, I_C=-10mA
		60	-		V_{CE}=-1V, I_C=-50mA
		30	-		V_{CE}=-1V, I_C=-100mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	-	-0.25	V	I_C=-10mA, I_B=-1mA
		-	-0.4		I_C=-50mA, I_B=-5mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	-0.65	-0.85	V	I_C=-10mA, I_B=-1mA
		-	-0.95		I_C=-50mA, I_B=-5mA

Small-signal Characteristics

Symbol	Description	Min.	Max.	Unit	Conditions
f_T	Current Gain-Bandwidth Product	250	-	MHz	V_{CE}=-20V, I_C=-10mA, f=100MHz
C_{OBO}	Output Capacitance	-	4.5	pF	V_{CB}=-5V, f=1.0MHz, I_E=0
C_{IBO}	Input Capacitance	-	10	pF	V_{EB}=-0.5V, f=1.0MHz, I_C=0
h_{ie}	Input Impedance	2.0	12	kohms	V_{CE}=-10V, I_C=-1mA, f=1kHz
h_{re}	Voltage Feedback Ratio	0.1	10	x 10^{-4}	V_{CE}=-10V, I_C=-1mA, f=1kHz
h_{fe}	Small-Signal Current Gain	100	400	-	V_{CE}=10V, I_C=-1mA, f=1kHz
h_{oe}	Output Admittance	3.0	60	UMHOS	V_{CE}=-10V, I_C=-1mA, f=1kHz
NF	Noise Figure	-	4.0	dB	V_{CE}=-5V, I_C=-100μA, Rs=1.0kohms, f=1kHz

Switching Characteristics

Symbol	Description	Min.	Max.	Unit	Conditions
t_d	Delay Time	-	35	ns	V_{CC}=-3V, V_{BE}=0.5V I_C=-10mA, I_{B1}=-1mA
t_r	Rise Time	-	35		
t_s	Storage Time	-	225		V_{CC}=-3V, I_C=-10mA, I_{B1}= I_{B2}=-1mA
t_f	Fall Time	-	75		

Equivalent Test Circuit

Fig.1- Delay and Rise Time

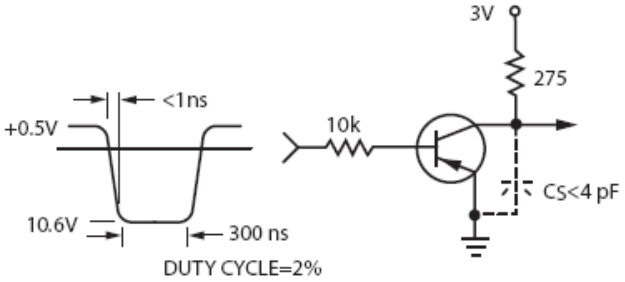
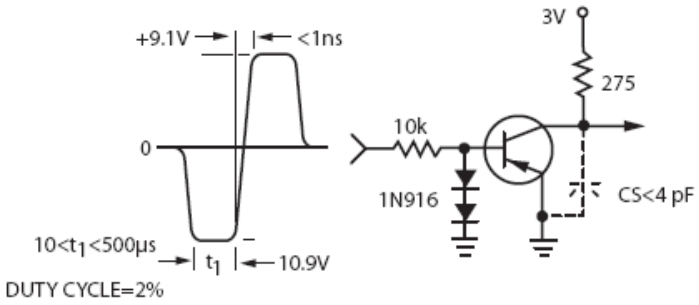


Fig.2- Storage and Fall Time



Total Shunt Capacitance of test jig and connectors

Typical Characteristics Curves (▬ T_J =25°C --- T_J =125°C)

Fig.3- Capacitance

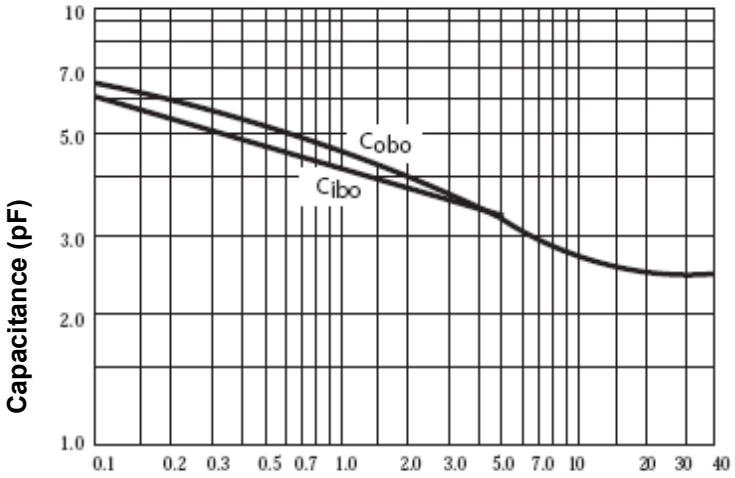


Fig.4- Charge Data

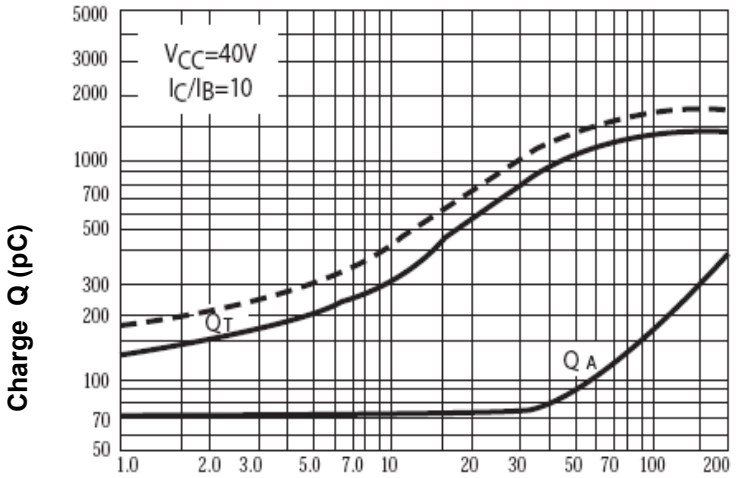


Fig.5- Turn-On Time

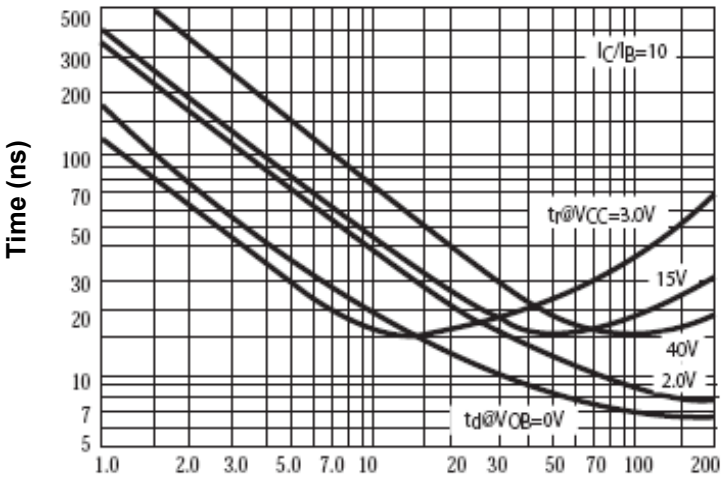
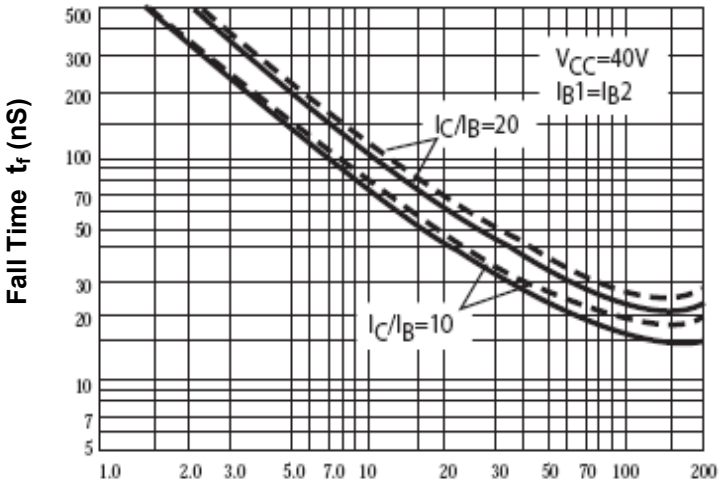


Fig.6- Fall Time



Typical Audio Small-Signal Characteristics Noise Figure Variations

(V_{CE}=-5.0 V. T_A=25°C, Bandwidth=1.0Hz)

Fig.7- Noise Figure

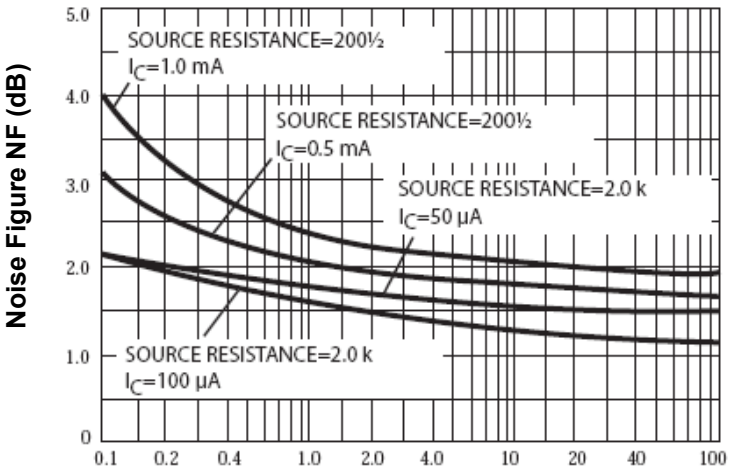
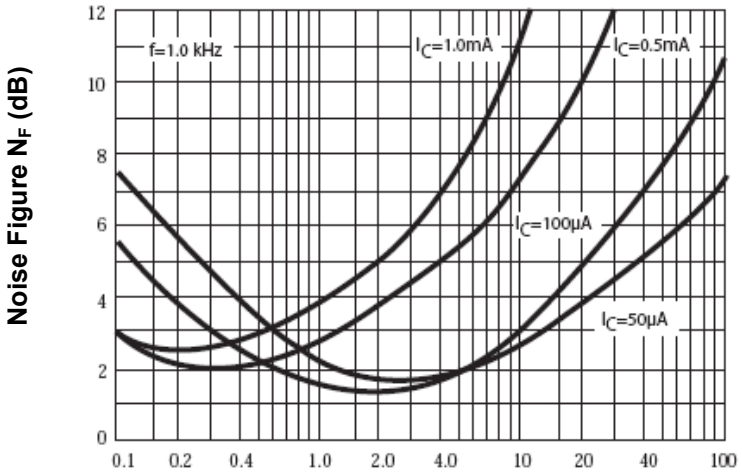


Fig.8- Noise Figure



h Parameters (V_{CE}=-10V, f=1.0kHz, T_A=25°C)

Fig.9- Current Gain

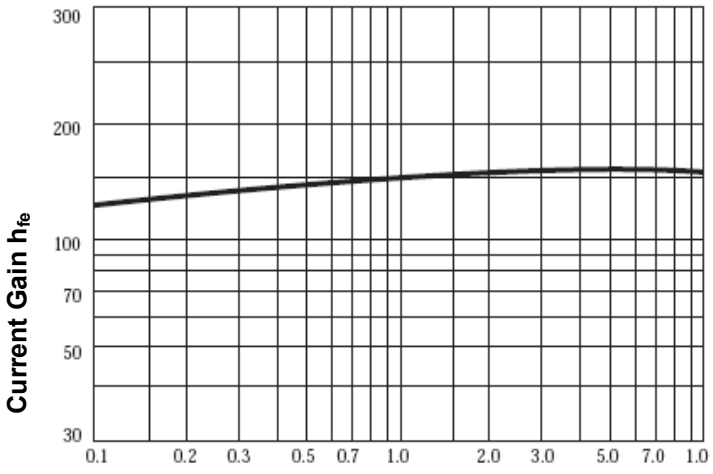


Fig.10- Output Admittance

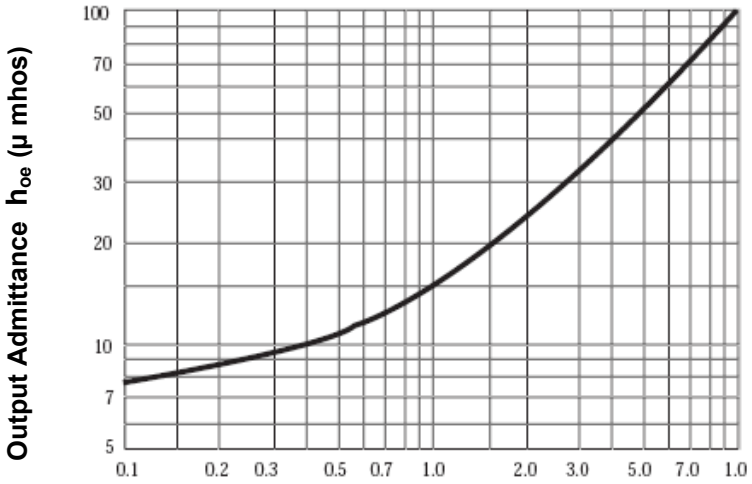


Fig.11- Input Impedance

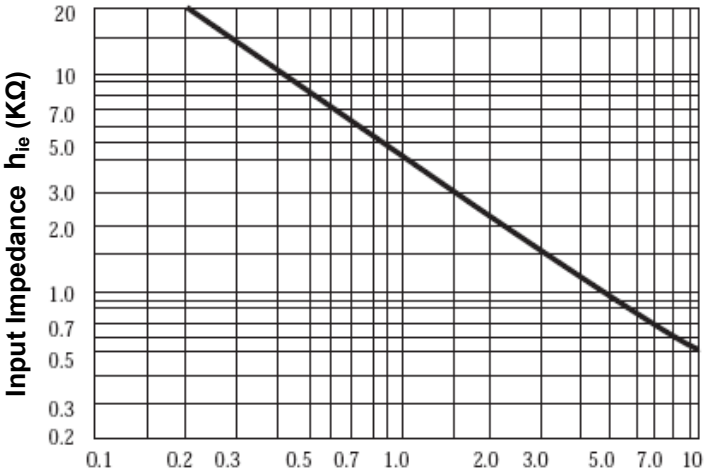
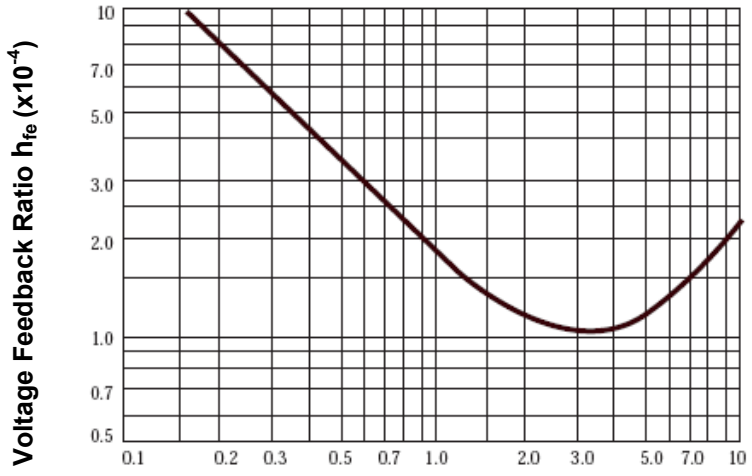


Fig.12- Voltage Feedback Ratio



Typical Static Characteristics

Fig.13- DC Current Gain

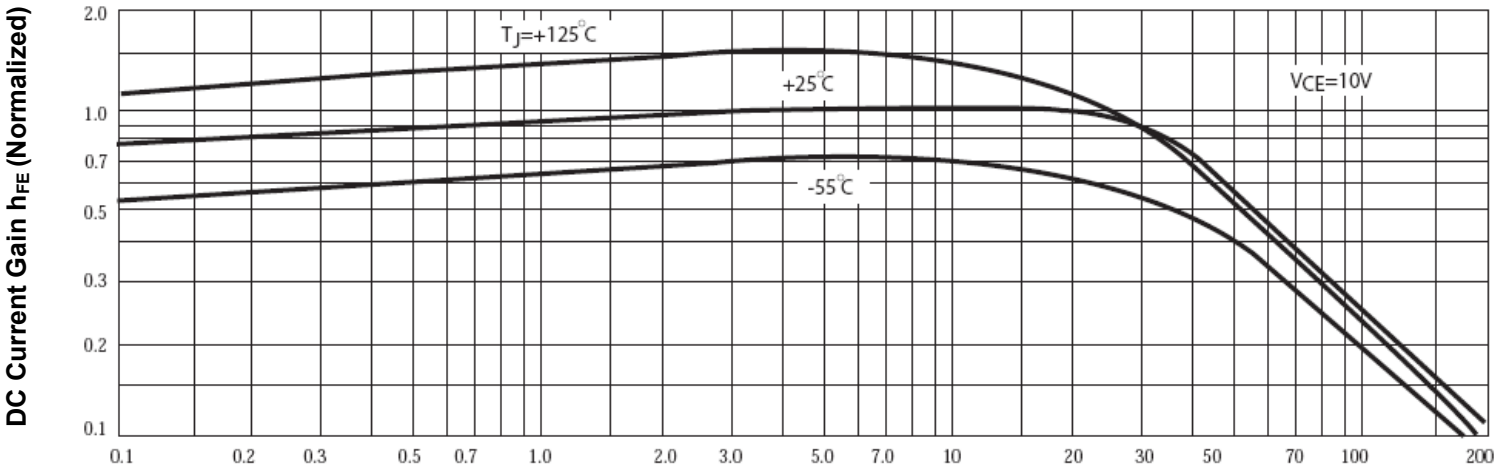


Fig.14- Collector Saturation Region

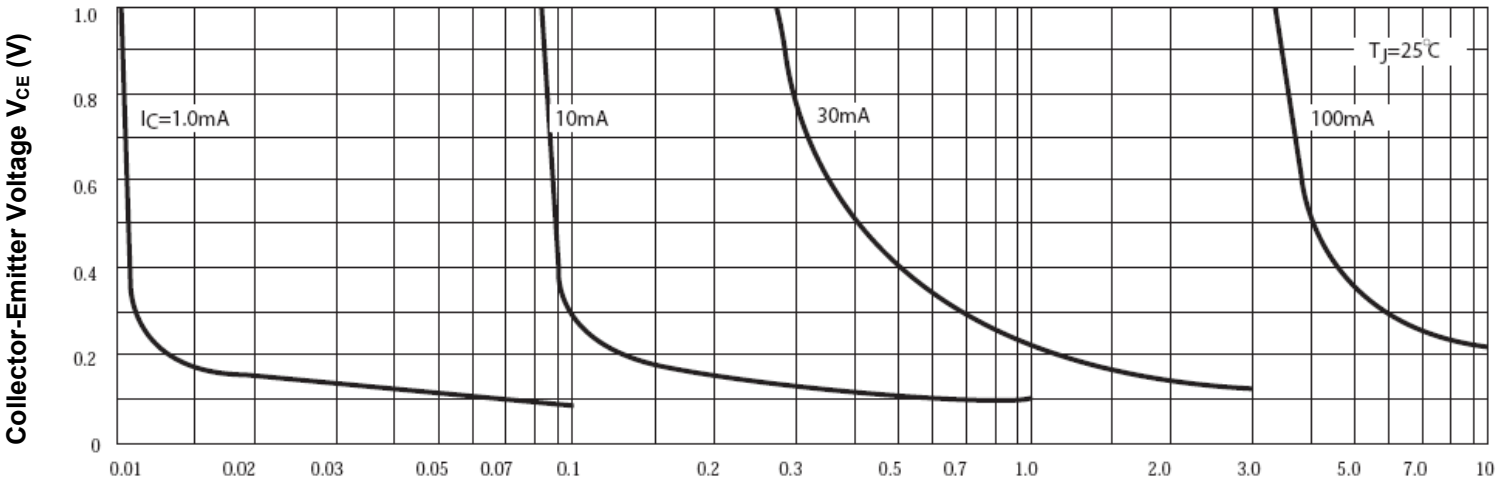


Fig.15- "On" Voltage

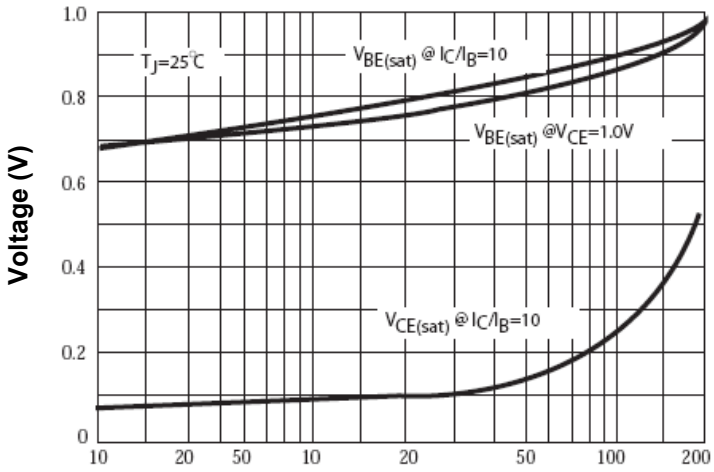
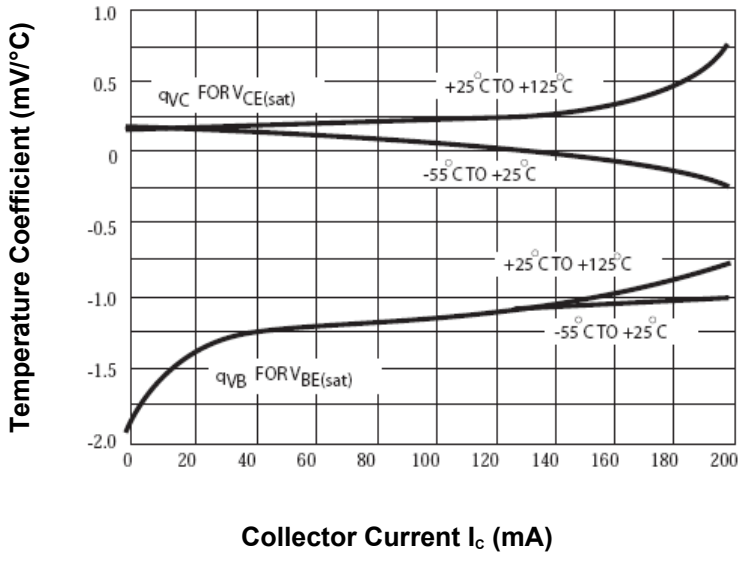


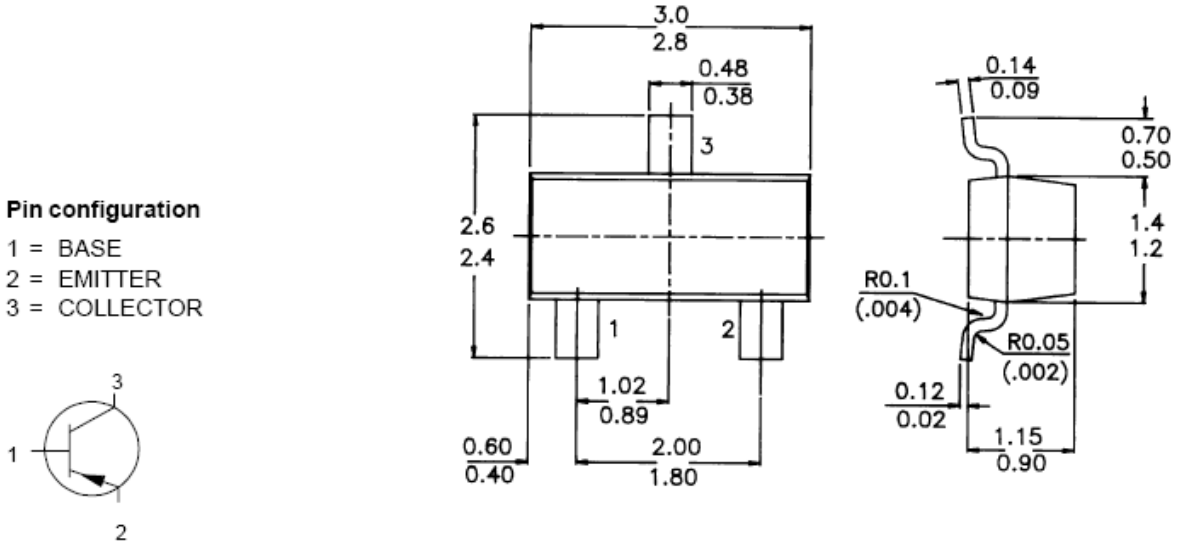
Fig.16- Temperature Coefficients



Device Marking: MMBT3906=2A

Dimensions in mm

SOT-23



How to contact us:

US HEADQUARTERS

28040 WEST HARRISON PARKWAY, VALENCIA, CA 91355-4162
Tel: (800) TAITRON (800) 247-2232 (661) 257-6060
Fax: (800) TAITFAX (800) 824-8329 (661) 257-6415
Email: taitron@taitroncomponents.com
Http://www.taitroncomponents.com

TAITRON COMPONENTS MEXICO, S.A .DE C.V.

BOULEVARD CENTRAL 5000 INTERIOR 5 PARQUE INDUSTRIAL ATITALAQUIA, HIDALGO C.P. 42970 MEXICO
Tel: +52-55-5560-1519
Fax: +52-55-5560-2190

TAITRON COMPONENTS INCORPORATED REPRESENTAÇÕES DO BRASIL LTDA

RUA DOMINGOS DE MORAIS, 2777, 2.ANDAR, SALA 24 SAÚDE - SÃO PAULO-SP 04035-001 BRAZIL
Tel: +55-11-5574-7949
Fax: +55-11-5572-0052

TAITRON COMPONENTS INCORPORATED, SHANGHAI REPRESENTATIVE OFFICE

METROBANK PLAZA, 1160 WEST YAN' AN ROAD, SUITE 1503, SHANGHAI, 200052, CHINA
Tel: +86-21-5424-9942
Fax: +86-21-5424-9931